



SEMiX® 3s

Trench IGBT Modules

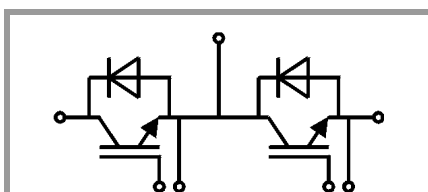
SEMiX353GB176HDs

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders



GB

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT				
V _{CES}			1700	V
I _C	T _j = 150 °C	T _c = 25 °C	353	A
		T _c = 80 °C	251	A
I _{Cnom}			225	A
I _{CRM}	I _{CRM} = 2xI _{Cnom}		450	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 1000 V V _{GE} ≤ 20 V V _{CES} ≤ 1700 V	T _j = 125 °C	10	μs
T _j			-55 ... 150	°C
Inverse diode				
I _F	T _j = 150 °C	T _c = 25 °C	428	A
		T _c = 80 °C	289	A
I _{Fnom}			225	A
I _{FRM}	I _{FRM} = 2xI _{Fnom}		450	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		1800	A
T _j			-40 ... 150	°C
Module				
I _{t(RMS)}	T _{terminal} = 80 °C		600	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 225\text{ A}$ $V_{GE} = 15\text{ V}$ chiplevel	$T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	2 2.5	2.45 2.9	V
V_{CE0}		$T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	1 0.9	1.2 1.1	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	4.4 6.9	5.6 8.0	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 9\text{ mA}$	5.2	5.8	6.4	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1700\text{ V}$	$T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	0.1	3	mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	19.9		nF
C_{oes}		$f = 1\text{ MHz}$	0.83		nF
C_{res}		$f = 1\text{ MHz}$	0.66		nF
Q_G	$V_{GE} = -8\text{ V...} + 15\text{ V}$		2100		nC
R_{Gint}	$T_j = 25\text{ °C}$		2.83		Ω
$t_{d(on)}$	$V_{CC} = 1200\text{ V}$ $I_C = 225\text{ A}$	$T_j = 125\text{ °C}$	250		ns
t_r	$V_{GE} = \pm 15\text{ V}$	$T_j = 125\text{ °C}$	75		ns
E_{on}	$R_{G on} = 5.6\text{ }\Omega$	$T_j = 125\text{ °C}$	155		mJ
$t_{d(off)}$	$R_{G off} = 5.6\text{ }\Omega$	$T_j = 125\text{ °C}$	930		ns
t_f		$T_j = 125\text{ °C}$	180		ns
E_{off}		$T_j = 125\text{ °C}$	85		mJ
$R_{th(j-c)}$	per IGBT			0.086	K/W



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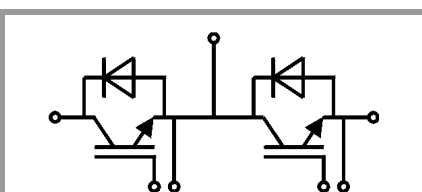
Features

- Homogeneous Si
- Trench = Trenchgate technology
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- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 225 A	T _j = 25 °C		1.6	1.75	V
	V _{GE} = 0 V chip	T _j = 125 °C		1.5	1.7	V
V _{F0}		T _j = 25 °C	0.9	1.1	1.3	V
		T _j = 125 °C	0.7	0.9	1.1	V
r _F		T _j = 25 °C	2.0	2.0	2.0	mΩ
		T _j = 125 °C	2.7	2.7	2.7	mΩ
I _{RRM}	I _F = 225 A	T _j = 125 °C	280			A
Q _{rr}	di/dt _{off} = 4000 A/μs	T _j = 125 °C	83			μC
E _{rr}	V _{GE} = -15 V V _{CC} = 1200 V	T _j = 125 °C	45			mJ
R _{th(j-c)}	per diode		0.13			K/W
Module						
L _{CE}			20			nH
R _{CC'+EE'}	res., terminal-chip	T _C = 25 °C	0.7			mΩ
		T _C = 125 °C	1			mΩ
R _{th(c-s)}	per module		0.04			K/W
M _s	to heat sink (M5)		3	5		Nm
M _t		to terminals (M6)	2.5	5		Nm
				Nm		
w			300			g
Temperatur Sensor						
R ₁₀₀	T _C =100°C (R ₂₅ =5 kΩ)		493 ± 5%			Ω
B _{100/125}	R _(T) =R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];		3550 ±2%			K



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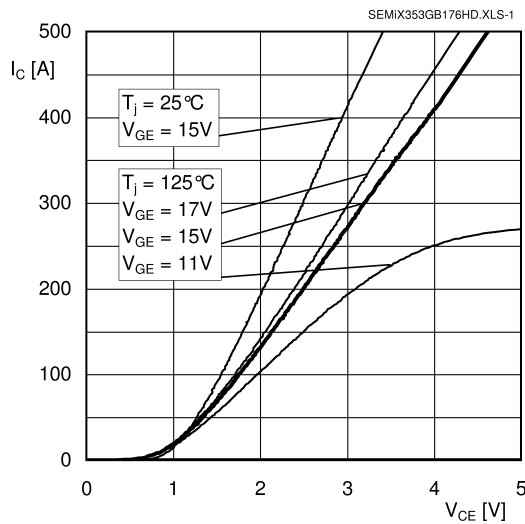


Fig. 1: Typ. output characteristic, inclusive $R_{CC} + EE'$

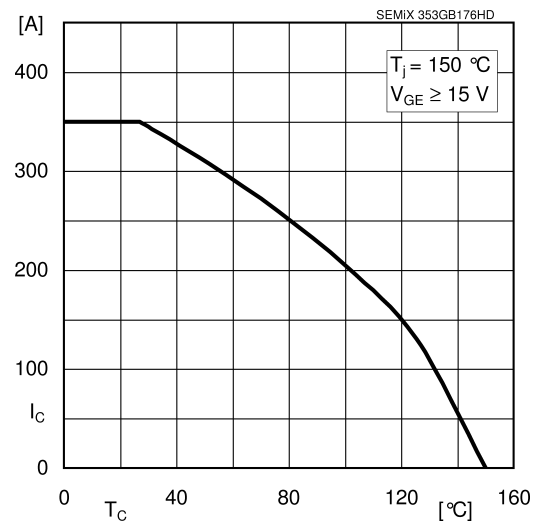


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

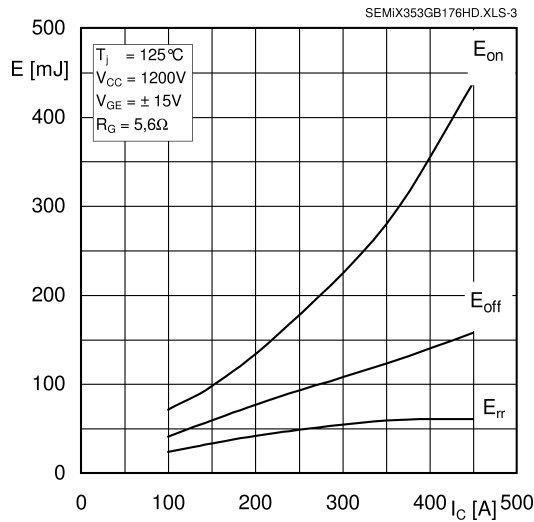


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

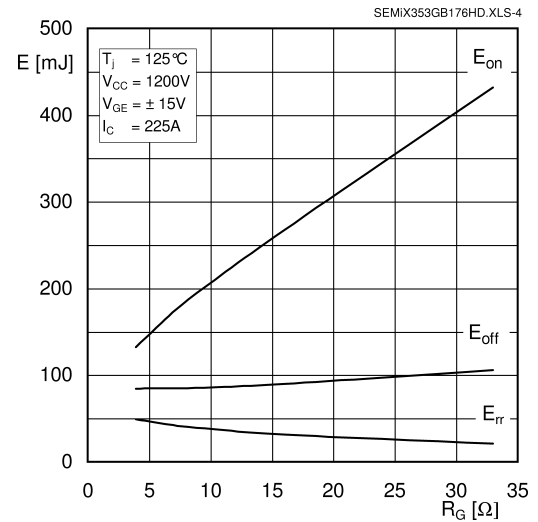


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

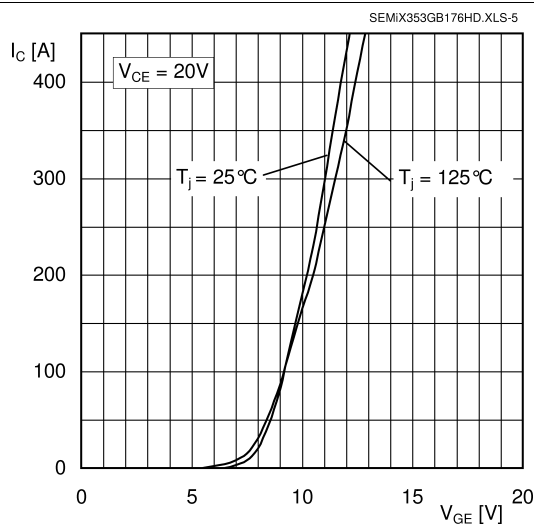


Fig. 5: Typ. transfer characteristic

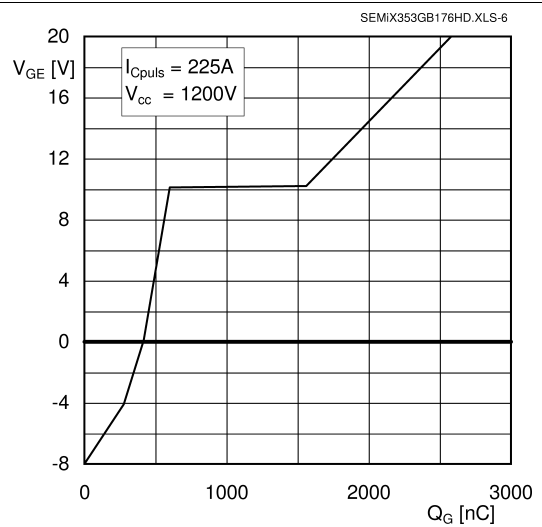


Fig. 6: Typ. gate charge characteristic

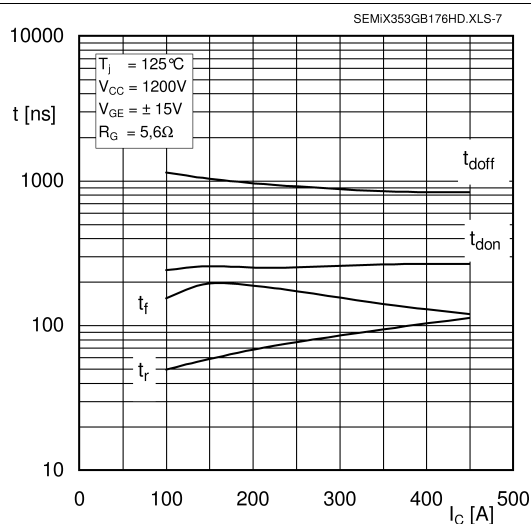
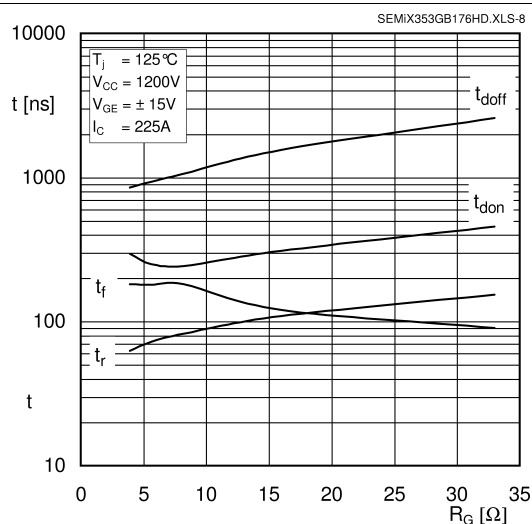
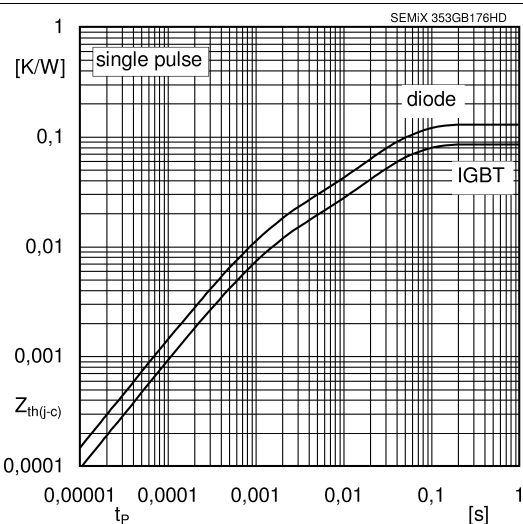
Fig. 7: Typ. switching times vs. I_C Fig. 8: Typ. switching times vs. gate resistor R_G 

Fig. 9: Typ. transient thermal impedance

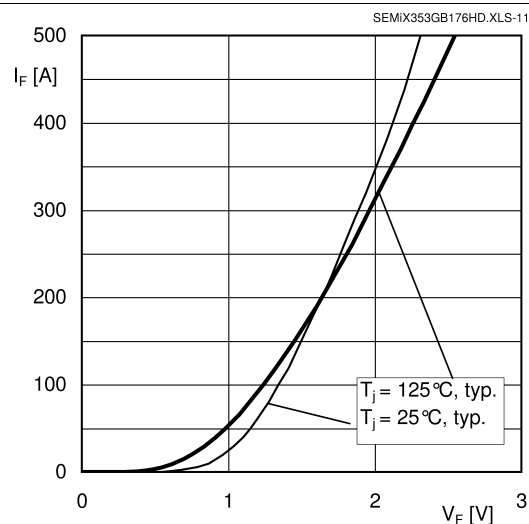
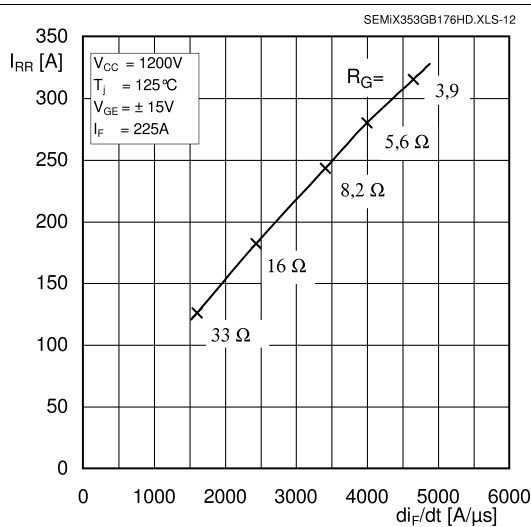
Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$ 

Fig. 11: Typ. CAL diode peak reverse recovery current

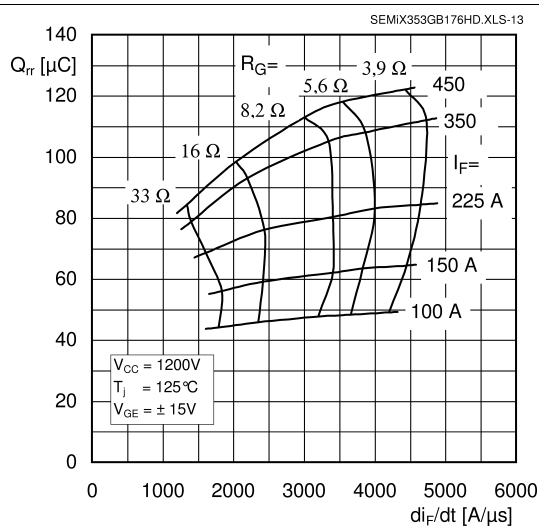


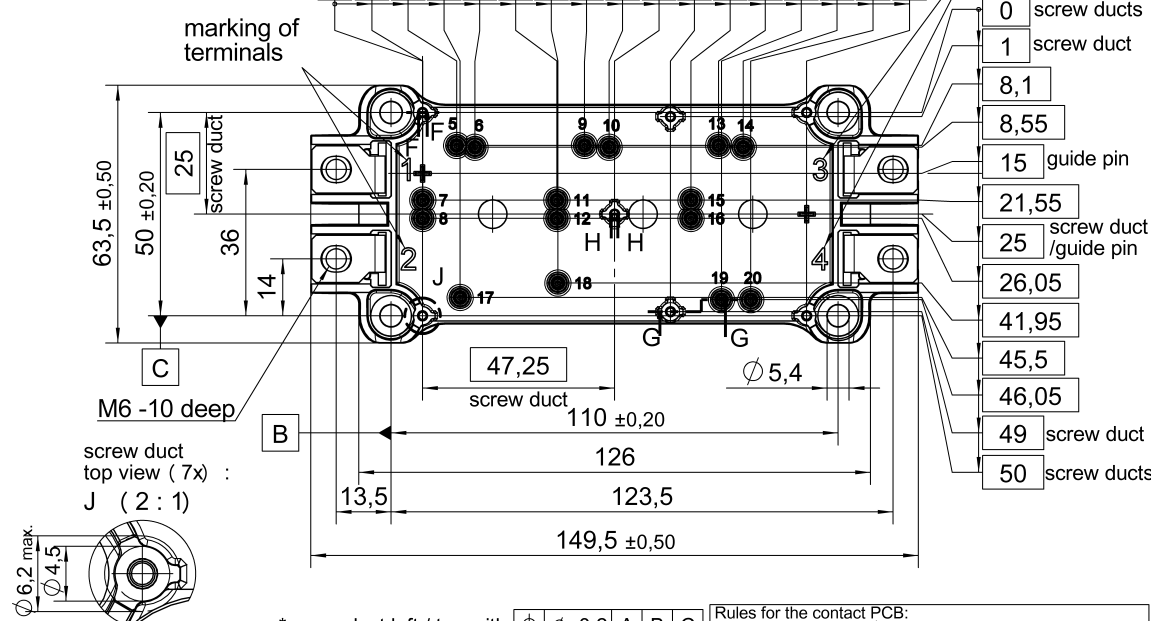
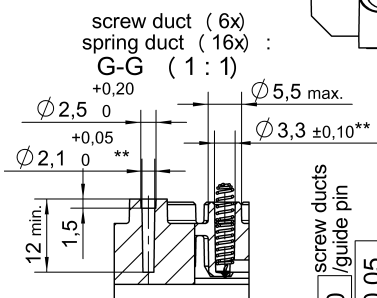
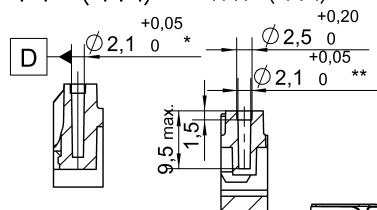
Fig. 12: Typ. CAL diode recovery charge

Case: SEMiX 3s

screw duct
(left top) :screw duct
(1x centre) :

F-F (1:1)

H-H (1:1)



*screw duct left / top with

ϕ	0,2	A	B	C
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**screw ducts / guide pins / spring ducts with

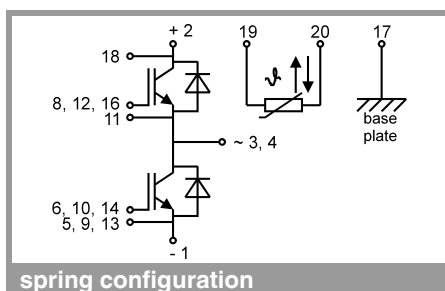
ϕ	0,2	A	D	C
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Rules for the contact PCB:

- holes guidepins = $\phi 4 \pm 0,1$ / position tolerance $\pm 0,1$
- holes for screws = $\phi 2,9 \pm 0,1$ / position tolerance $\pm 0,1$
- spring contact pad = $\phi 3,6 \pm 0,1$ / position tolerance $\pm 0,1$

general tolerance:
ISO 2768-mK
ISO 8015All measures in Z-direction
valid when mounted to heat sink

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.